

## Plan 3 – Full Technical Rationale + Formula-Supported Explanation

This PDF preserves formulas without Markdown rendering issues.—

### 3.1 Mean Free Path $\lambda$

$$\lambda = k_B * T / (\sqrt{2} * \pi * d^2 * P)$$

Condition:

$\lambda \gg L_{\text{channel}}$  → ballistic transport.

—

### 3.2 Fowler–Nordheim Injection

$$J = A * (E^2 / \phi) * \exp(-B * \phi^{(3/2)} / E)$$

Purpose: control electron injection energy.

—

### 3.3 Ramsauer–Townsend Scattering Minimum

$\sigma(E) \rightarrow$  minimum at specific electron energies.

Meaning: inert gas becomes nearly transparent.

--

### 3.4 Disjoining Pressure (Liquid Confinement in 1.0)

$$\Pi(h) = \Pi * \exp(-h / \lambda_D)$$

Used to justify stable nanoscale gas layer.

--

### 3.5 Electrowetting (Instability of Liquid-Based 1.0)

$$\cos\theta(V) = \cos\theta + (\epsilon * \epsilon_r * V^2) / (2 * \gamma * t)$$

Explains why liquid moves under electric fields.—

### 3.6 Pinning Force (Solid SAM Layer in 2.0)

$$F_{pin} = \Delta\gamma * L$$

Solid interface → no creep, stable confinement.

--

### 3.7 Marangoni Number (Interface Oscillation Check)

$$Ma = |\frac{d\gamma}{dT}| * L * \Delta T / (\mu * \alpha)$$

At nanoscale:  $Ma \ll 1 \rightarrow$  interface stable.

--

### 3.8 Transit Time vs Scattering Time

$$\tau_{scattering} \gg \tau_{transit}$$

Electron transit across 100 nm:  $\sim 1e-13$  s.

Disturbances occur slower → electron unaffected.

--

### 3.9 Joule Heating Reduction

$$P = I^2 * R$$

If  $R$  is extremely small  $\rightarrow$  negligible heating.

--

### 3.10 Physical Closure Summary

- Gas confinement stable (1.0 & 2.0)
- Scattering suppressed ( $RT + \lambda/L$ )
- Electron energy controllable (F-N)
- Solid interface stable (SAM pinning)
- Transit outruns disturbances ( $\tau$ )
- Joule heating minimized
- No superconductivity mechanism involved